



Deadlines

Abstract submission 30 April, 2007
 Early registration 15 August, 2007

Abstract submission exclusively takes place via the DRIP XII website.

Conference Fee

Accompanying person 350,00 €
 Students 375,00 €
 Participants 475,00 €

For registration after August 15th, an additional fee of 50,00 € will be charged.

Conference Proceedings

Proceedings will be published in the SPRINGER Journal of Materials Science: Materials in Electronics. There will be a page limit of 4 and 6 printed pages for regular contributions (talks and posters) and invited talks, respectively.

Travel Grants

There is a limited number of travel grants which will be awarded to young scientists. Terms and conditions are published on the conference website.

Further Information

Please contact us if you would like to be put on the DRIP mailing list.

For more details, updated information, and the conference program please visit the conference website: <http://www.drip12.de>

DRIP XII Berlin

second announcement



Contact

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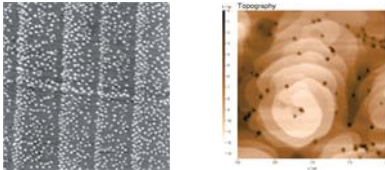
**12th International Conference on
 Defects-Recognition, Imaging
 & Physics in Semiconductors**



The International Conference on Defects - Recognition, Imaging and Physics in Semiconductors (DRIP) is a conference on the physics of semiconductors with special emphasis on defects covering application aspects as well as fundamental questions regarding the physics of defects.

Main Areas of Interest are

- The physics of active defects in elemental and compound semiconductors
- Experimental ways to get information on defects by means of imaging and spectroscopy
- The effects of imperfections on the properties of bulk semiconductors, epitaxial layers, and interfaces
- The qualification and reliability of electronic or optoelectronic devices in relation to the defects or imperfections in the materials assessed by imaging or mapping



Within the conference a special session “Defects in Devices” is offered. This session is supported by BRIGHTER.EU, an integrated project which is funded by the European Commission.

Venue

DRIP XII will be held in the Marriott Courtyard Hotel in Berlin. This four star hotel is located on the banks of the river Dahme opposite the old town of Köpenick and the castle.

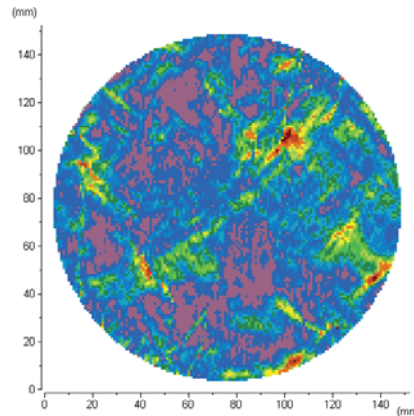
Single and double rooms will be available at a special rate of 75 € per night for conference attendees and accompanying persons (also valid for additional days before or after the conference).



<http://marriott.com/property/propertypage/BERCY>

Other accommodations are indicated on the website. All reservations should be made directly with the hotels.

- New frontiers of atomic-scale-defect assessment using nano-probe methods (STM, AFM, SNOM, ballistic electron energy microscopy, ...)
- Submicron 2D and 3D optical imaging (classical and UV microscopy, confocal microscopy, scanning interference microscopy, laser scanning tomography, ...)
- Spectroscopic techniques (PL and micro-PL, Raman and micro-Raman, ...)
- Contactless electrical characterization techniques
- Defect imaging using electrical transport characterization techniques
- Electron beam methods (TEM, EBIC, cathodoluminescence, ...)
- X-ray based techniques (topography, diffractometry, fluorescence, ...)
- Defect mapping (of any type) over large area wafers
- Defect analysis in degraded optoelectronic and electronic devices
- Strategies for correlation and interpretation of results of different techniques
- In-situ diagnostics and process control
- Defects and degradation of organic semiconductors and devices
- Specific sessions on defects in various classes of semiconductor materials with respect to their fields of application (bulk or epitaxial Si, III-V's for optoelectronics, III-V's for micro-wave electronics, wide bandgap semiconductors, Si-based thin films for large-area electronics, ...)



Invited Speakers (Tentative List as of January 2007)

- Martin Albrecht, Institut für Kristallzüchtung (Germany)
- Tilo Baumbach, Universität Karlsruhe (Germany)
- Tonio Buonassisi, Evergreen Solar, Inc. (USA)
- Mark S. Goorsky, University of California, Los Angeles (USA)
- Colin Humphreys, University of Cambridge (UK)
- Martin Kuball, University of Bristol (UK)
- Abdelmajid Mesli, Laboratoire InESS (France)
- Julien Nagle, Thales Research and Technology (France)
- James Speck, University of California, Santa Barbara (USA)
- Eicke Weber, Fraunhofer Institut für Solare Energiesysteme (Germany)
- Hiroshi Yamada-Kaneta, Niigata University (Japan)

Chair Persons

- Jens W. Tomm, Germany
- Ute Zeimer, Germany

Scientific Program Committee

- Roy Blunt, UK
- Daniel Cassidy, Canada
- Roberto Fornari, Germany
- Dagmar Gerthsen, Germany
- Nancy Giles, USA
- Arndt Jaeger, Germany
- Abram Jakubowicz, Switzerland
- Bernd Jenichen, Germany
- Martin Kittler, Germany
- Samuil G. Konnikov, Russia
- Anna Kozłowska, Poland
- Christoph Lienau, Germany
- Dieter Neher, Germany
- Thien-Phap Nguyen, France
- Masayoshi Yamada, Japan
- Deren Yang, China

Organizing Committee (Germany)

- Birgit Helm, Petra Immerz, Uta Juda, Maria Krichler, Helen Lawrenz, Renate Rondt, Sandy Schwirzke-Schaaf, Mathias Ziegler